

-- 13. The thin film transistor according to Claim 2, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different film thickness compared to other regions. --

-- 14. The thin film transistor according to Claim 3, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different film thickness compared to other regions. --

-- 15. The thin film transistor according to Claim 2, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different surface positions compared to other regions. --

-- 16. The thin film transistor according to Claim 3, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different surface positions compared to other regions. --